

GaAlAs-IR-Lumineszenzdiode (880 nm) GaAlAs Infrared Emitters (880 nm)

SFH 484

SFH 485



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SFH 485

Wesentliche Merkmale

- GaAlAs-LED mit sehr hohem Wirkungsgrad
- Hohe Zuverlässigkeit
- Gute spektrale Anpassung an Si-Fotoempfänger
- Gegurtet lieferbar (im Ammo-Pack)
- Gruppiert lieferbar
- SFH 484: Gehäusegleich mit LD 274
- SFH 485: Gehäusegleich mit SFH 300, SFH 203

Features

- Very highly efficient GaAlAs-LED
- High reliability
- Spectral match with silicon photodetectors
- Available on tape and reel (in Ammopack)
- Available in bins
- SFH 484: Same package as LD 274
- SFH 485: Same package as SFH 300, SFH 203

Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern
- Gerätefernsteuerungen für Gleich- und Wechsellichtbetrieb
- Rauchmelder (UL-Freigabe)
- Sensorik
- Diskrete Lichtschranken

Applications

- IR remote control of hi-fi and TV-sets, video tape recorders, dimmers
- Remote control for steady and varying intensity
- Smoke detectors (UL-approval)
- Sensor technology
- Discrete interrupters

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 484	Q62703-Q1092	5-mm-LED-Gehäuse (T 1 ³ / ₄), klares violettes Epoxy-Gießharz, Anschlüsse im 2.54-mm-Raster (1/10"), Anodenkennzeichnung: kürzerer Anschluß
SFH 484-2	Q62703-Q1756	
SFH 485	Q62703-Q1093	5 mm LED package (T 1 ³ / ₄), violet-colored epoxy resin, solder tabs lead spacing 2.54 mm (1/10"), anode marking: short lead
SFH 485-2	Q62703-Q1547	

Grenzwerte ($T_A = 25\text{ °C}$)

Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Durchlaßstrom Forward current	I_F	100	mA
Stoßstrom, $t_p = 10\text{ }\mu\text{s}$, $D = 0$ Surge current	I_{FSM}	2.5	A
Verlustleistung Power dissipation	P_{tot}	200	mW
Wärmewiderstand, freie Beinchenlänge max. 10 mm Thermal resistance, lead length between package bottom and PC-board max. 10 mm	R_{thJA}	375	K/W

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$	λ_{peak}	880	nm
Spektrale Bandbreite bei 50% von I_{rel} Spectral bandwidth at 50% of I_{rel} $I_F = 100\text{ mA}$	$\Delta\lambda$	80	nm
Abstrahlwinkel Half angle SFH 484 SFH 485	φ φ	± 8 ± 20	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm ²
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm
Abstand Chipoberfläche bis Linsenscheitel Distance chip front to lens top SFH 484 SFH 485	H H	5.1 ... 5.7 4.2 ... 4.8	mm mm
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $R_L = 50\text{ }\Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $R_L = 50\text{ }\Omega$	t_r , t_f	0.6/0.5	μs
Kapazität Capacitance $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_o	15	pF
Durchlaßspannung Forward voltage $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F V_F	1.50 (≤ 1.8) 3.00 (≤ 3.8)	V V
Sperrstrom, Reverse current $V_R = 5\text{ V}$	I_R	0.01 (≤ 1)	μA
Gesamtstrahlungsfluß, Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	Φ_e	25	mW

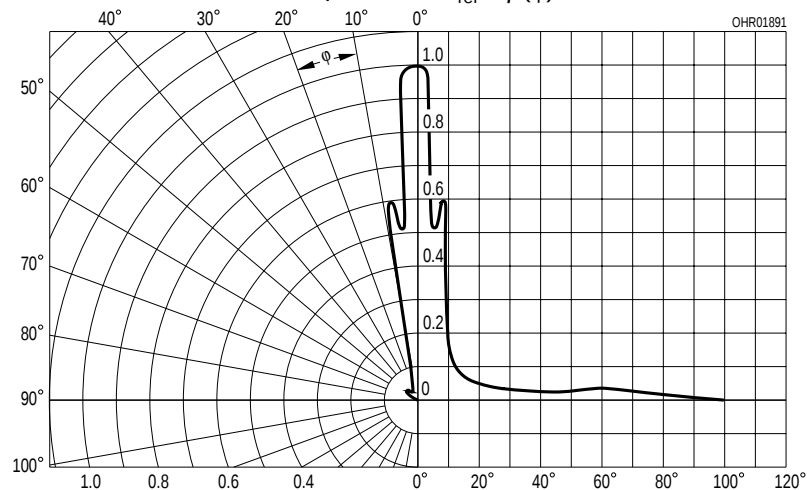
Kennwerte ($T_A = 25\text{ °C}$)**Characteristics** (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_I	- 0.5	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 2	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	0.25	nm/K

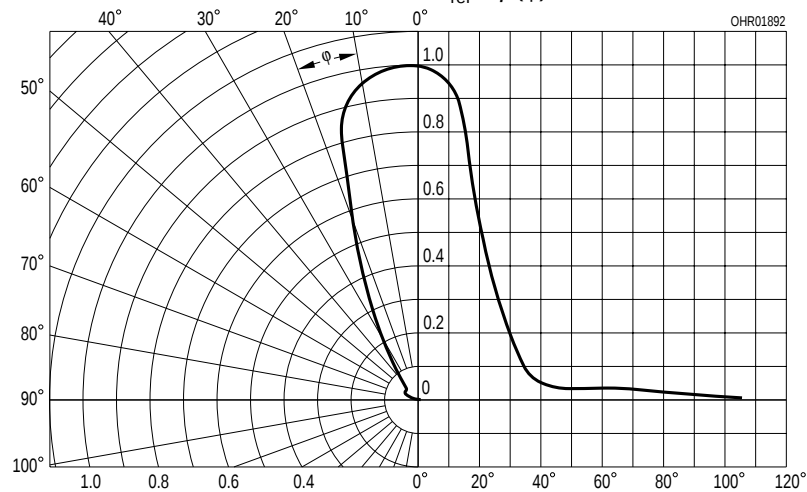
Gruppierung der Strahlstärke I_e in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.001\text{ sr}$ bei SFH 484 bzw. $\Omega = 0.01\text{ sr}$ bei SFH 485**Grouping of Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.001\text{ sr}$ at SFH 484 or $\Omega = 0.01\text{ sr}$ at SFH 485

Bezeichnung Parameter	Symbol	Wert Value					Einheit Unit
		SFH 484	SFH 484-1	SFH 484-2	SFH 485	SFH 485-2	
Strahlstärke Radiant intensity $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	$I_{e\text{ min}}$ $I_{e\text{ max}}$	50 -	50 100	80 -	25 160	25 100	mW/sr mW/sr
Strahlstärke Radiant intensity $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	$I_{e\text{ typ.}}$	800	700	900	300	340	mW/sr

Radiation Characteristics, SFH 484 $I_{\text{rel}} = f(\varphi)$

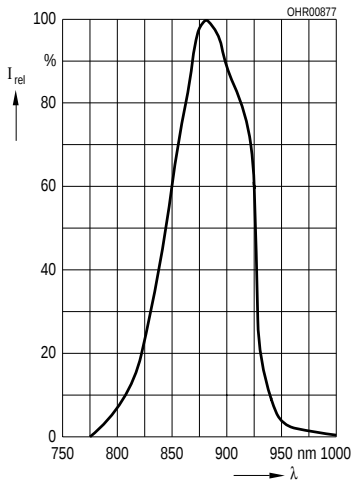


Radiation Characteristics SFH 485 $I_{\text{rel}} = f(\varphi)$



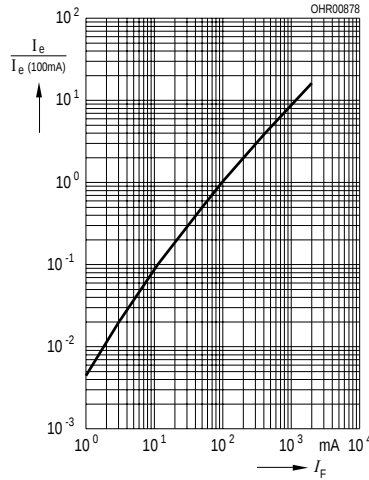
Relative Spectral Emission

$$I_{rel} = f(\lambda)$$



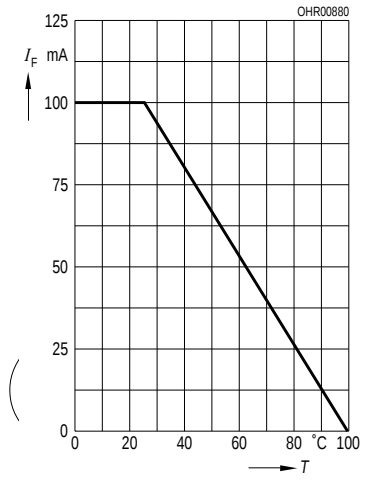
$$\text{Radiant Intensity } \frac{I_e}{I_e(100 \text{ mA})} = f(I_F)$$

Single pulse, $t_p = 20 \mu\text{s}$



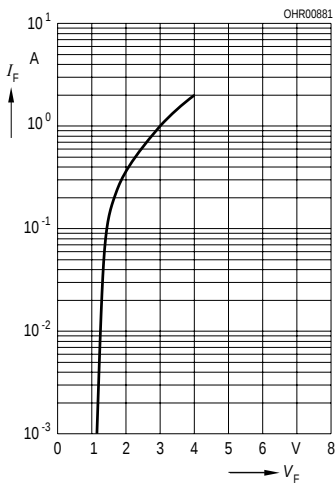
Max. Permissible Forward Current

$$I_F = f(T_A)$$



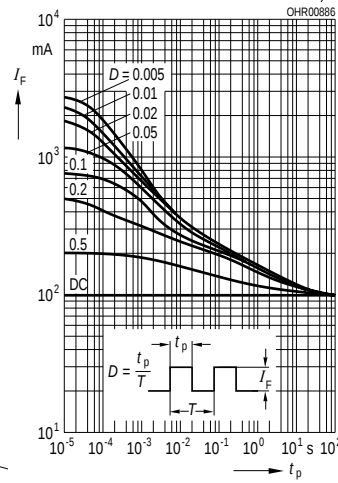
Forward Current

$$I_F = f(V_F), \text{ single pulse, } t_p = 20 \mu\text{s}$$



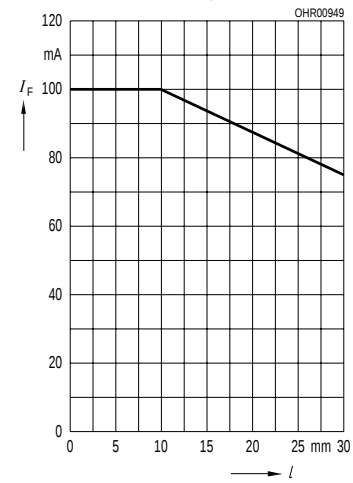
Permissible Pulse Handling Capability

$$I_F = f(\tau), T_A = 25^\circ\text{C}, \text{ duty cycle } D = \text{parameter}$$



Forward Current vs. Lead Length between the Package Bottom and the PC-Board

$$I_F = f(l), T_A = 25^\circ\text{C}$$



Technical drawing of a 6305 ball bearing showing dimensions in millimeters (mm) and inches (in). The drawing includes a side view and an end view.

Side View Dimensions:

- Outer Diameter: 9.0 (0.354)
- Inner Diameter: 7.8 (0.307)
- Width: 7.5 (0.295)
- Top Fillet Radius: 0.6 (0.024)
- Bottom Fillet Radius: 0.4 (0.016)
- Spacing: 2.54 (0.100)
- Top Chamfer: 0.8 (0.031)
- Bottom Chamfer: 0.5 (0.020)
- Top Hole Diameter: $\varnothing 5.1$ (0.201)
- Bottom Hole Diameter: $\varnothing 4.8$ (0.189)
- Top Hole Position: 4.8 (0.189)
- Bottom Hole Position: 4.2 (0.165)
- Chip Position: 29 (1.142) / 27 (1.063)
- Area not flat: Indicated by a line pointing to the top surface.

End View Dimensions:

- Outer Diameter: 5.9 (0.232)
- Inner Diameter: 5.5 (0.217)
- Top Hole Position: 0.6 (0.024)
- Bottom Hole Position: 0.4 (0.016)
- Cathode: Indicated by a line pointing to the top surface.

GEY6305

Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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